

# BC857BM,315 Datasheet



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DiGi Electronics Part Number BC857BM,315-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number BC857BM,315

Description TRANS PNP 45V 0.1A SOT883

Detailed Description Bipolar (BJT) Transistor PNP 45 V 100 mA 100MHz 1

50 mW Surface Mount SOT-883



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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# **Purchase and inquiry**

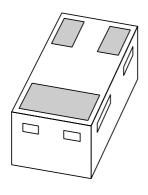
Manufacturer Product Number:	Manufacturer:
BC857BM,315	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	100 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
45 V	400mV @ 5mA, 100mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
15nA (ICBO)	220 @ 2mA, 5V
Power - Max:	Frequency - Transition:
150 mW	100MHz
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
SC-101, SOT-883	SOT-883
Base Product Number:	
BC857	

# **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0075	

# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# BC857M series PNP general purpose transistors

Product data sheet Supersedes data of 2003 Jul 15



# PNP general purpose transistors

# **BC857M series**

#### **FEATURES**

- Leadless ultra small plastic package (1 mm × 0.6 mm × 0.5 mm)
- Board space 1.3 × 0.9 mm
- Power dissipation comparable to SOT23.

#### **APPLICATIONS**

- General purpose small signal DC
- Low and medium frequency AC applications
- Mobile communications, digital (still) cameras, PDAs, PCMCIA cards.

#### **DESCRIPTION**

PNP general purpose transistor in a SOT883 leadless ultra small plastic package.

NPN complement: BC847M series.

#### **MARKING**

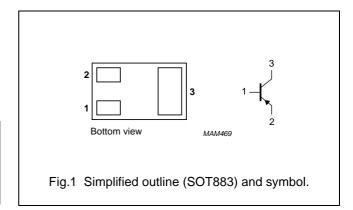
TYPE NUMBER	MARKING CODE
BC857AM	D1
BC857BM	D2
BC857CM	D3

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	-45	V
I <sub>C</sub>	collector current (DC)	-100	mA
I <sub>CM</sub>	peak collector current	-200	mA

#### **PINNING**

PIN	DESCRIPTION
1	base
2	emitter
3	collector



# **ORDERING INFORMATION**

TYPE NUMBER	PACKAGE			
THE NUMBER	NAME	NAME DESCRIPTION VE		
BC857AM	_	Leadless ultra small plastic package; 3 solder lands; body	SOT883	
BC857BM		1.0 x 0.6 x 0.5 mm		
BC857CM				

# PNP general purpose transistors

BC857M series

# **LIMITING VALUES**

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-45	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V
Ic	collector current (DC)		_	-100	mA
I <sub>CM</sub>	peak collector current		_	-200	mA
I <sub>BM</sub>	peak base current		_	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
		note 1	_	250	mW
		note 2	_	430	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### **Notes**

- 1. Refer to SOT883 standard mounting conditions (footprint), FR4 with 60  $\mu$ m copper strip line.
- 2. Device mounted on a FR4 printed-circuit board, single-sided copper, mounting pad for collector 1 cm<sup>2</sup>.

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air		
		note 1	500	K/W
		note 2	290	K/W

# **Notes**

- 1. Refer to SOT883 standard mounting conditions (footprint), FR4 with 60 μm copper strip line.
- 2. Device mounted on a FR4 printed-circuit board, single-sided copper, mounting pad for collector 1 cm<sup>2</sup>.

# PNP general purpose transistors

# BC857M series

# **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0$	_	-15	nA
		$V_{CB} = -30 \text{ V}; I_E = 0; T_j = 150 ^{\circ}\text{C}$	_	-5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$			
	BC857AM		125	250	
	BC857BM		220	475	
	BC857CM		420	800	
$V_{BE}$	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-600	-750	mV
		$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}$	_	-820	mV
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	-200	mV
		$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}; \text{ note 1}$	-	-400	mV
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	-	2.5	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V; } I_{C} = -10 \text{ mA;}$ f = 100 MHz	100	_	MHz
F	noise figure	$I_C$ = -200 μA; $V_{CE}$ = -5 V; $R_S$ = 2 kΩ; f = 1 kHz; B = 200 Hz	_	10	dB

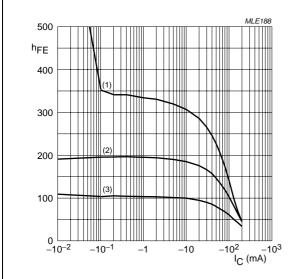
# Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

# PNP general purpose transistors

# BC857M series

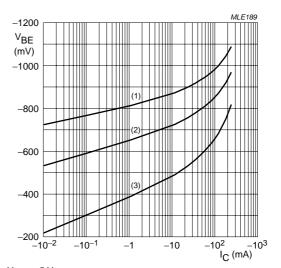
#### **GRAPHICAL INFORMATION BC857AM**



 $V_{CE} = -5 V.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

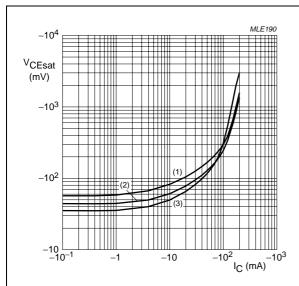
Fig.2 DC current gain; typical values.



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3) T<sub>amb</sub> = 150 °C.

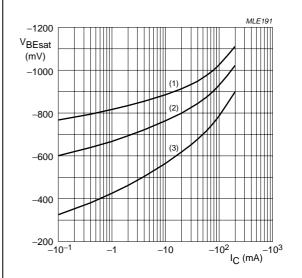
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$ .

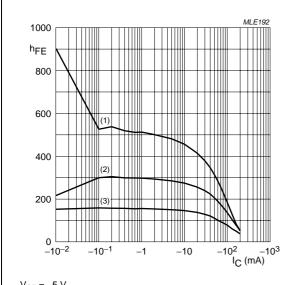
- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

# PNP general purpose transistors

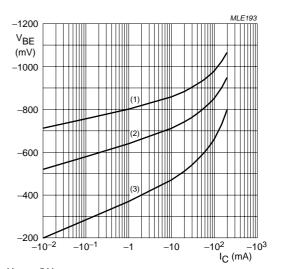
# BC857M series

#### **GRAPHICAL INFORMATION BC857BM**



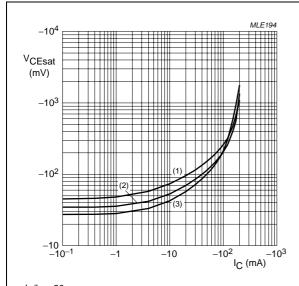
- $V_{CE} = -5 V.$
- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.6 DC current gain; typical values.



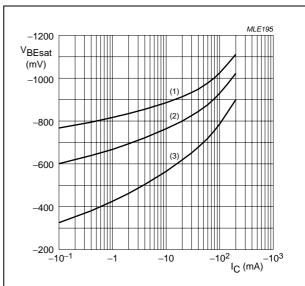
- $V_{CE} = -5 \text{ V}.$
- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3) T<sub>amb</sub> = 150 °C.

Fig.7 Base-emitter voltage as a function of collector current; typical values.



- $I_{\rm C}/I_{\rm B} = 20.$
- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



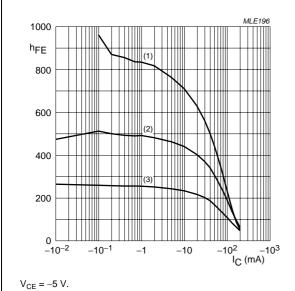
- $I_{\rm C}/I_{\rm B} = 20.$
- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.

# PNP general purpose transistors

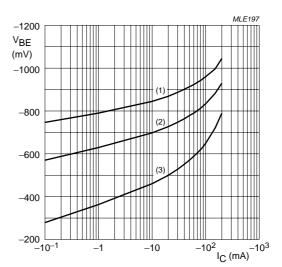
# BC857M series

#### **GRAPHICAL INFORMATION BC857CM**



- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

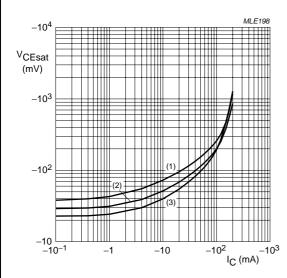
Fig.10 DC current gain; typical values.



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2) T<sub>amb</sub> = 25 °C.
- (3) T<sub>amb</sub> = 150 °C.

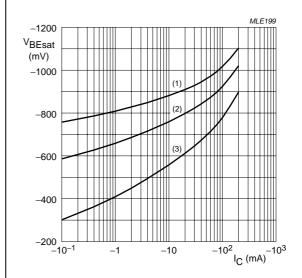
Fig.11 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

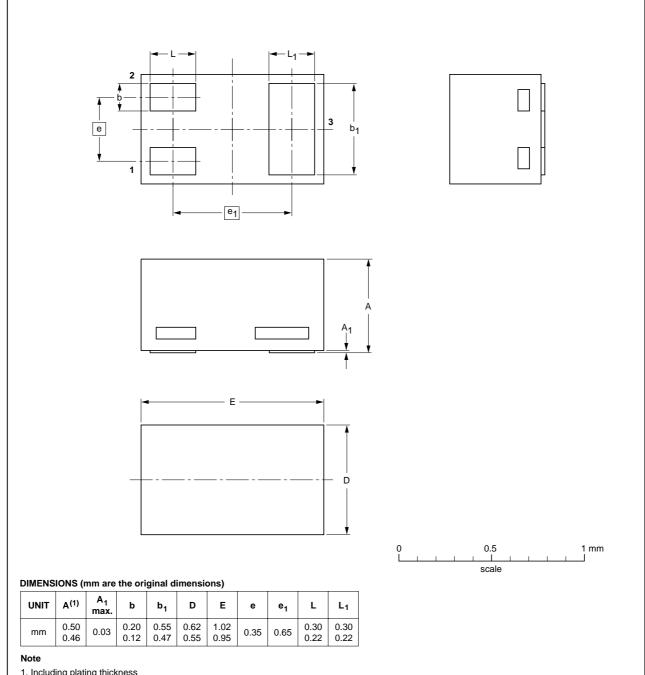
# PNP general purpose transistors

# BC857M series

# **PACKAGE OUTLINE**

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

**SOT883** 



1. Including plating thickness

OUTLINE		REFERENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT883			SC-101			<del>03-02-05</del> 03-04-03

# PNP general purpose transistors

# BC857M series

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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#### **Contact information**

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